1. (amended) A method for manufacturing a semiconductor device, the method comprising the steps of:

(a) forming a gate dielectric layer on a semiconductor layer;

(b) forming a first conductive layer having a specified pattern on the gate dielectric layer;

(c) forming sidewall insulation layers on side walls of the first conductive layer;

(d) forming a source region and a drain region in the semiconductor layer;

(e) depositing a first insulation layer that covers the first conductive layer and the sidewall insulation layers, the first insulation layer comprising a material different from that of the sidewall insulation layers;

(f) planarizing the first insulation layer until an upper surface of the first conductive layer is exposed;

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(g) removing a part of the first conductive layer in a manner that the gate dielectric layer is not exposed to thereby form a recessed section on the first conductive layer between the sidewall insulation layers;

(h) partially filling the recessed section with a second conductive layer to form a gate electrode that includes at least the first conductive layer and the second conductive layer;

(i) forming a second insulation layer that fills the recessed section on the second conductive layer, the second insulation layer comprising a material different from that of the first insulation layer;

(j) etching the first insulation layer to form a first through hole that reaches the source region or the drain region; and

(k) forming a first contact layer in the first through hole.

2. (amended) A method for manufacturing a semiconductor device according to claim 1, wherein, in the step (j), the second insulation layer and the sidewall insulation layers comprise a material that is more resistant to an etchant than the first insulation layer.

3. (amended) A method for manufacturing a semiconductor device according to claim 1, wherein the first conductive layer is a silicon layer, and the step (h) includes the steps of

(h – 1) depositing a metal layer for siliciding the first conductive layer on the first conductive layer; and

(h – 2) siliciding the first conductive layer to form a silicide layer.

4. (amended) A method for manufacturing a semiconductor device according to claim 1, further comprising:

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(l) forming a third insulation layer on the first insulation layer and the second insulation layer;

(m) etching the third insulation layer to form a second through hole; and

(n) forming a second contact layer in the second through hole, wherein the second through hole overlaps the first through hole.

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9. (amended) A method for manufacturing a semiconductor device, comprising:

forming a gate dielectric layer on a semiconductor layer;

forming a first conductive layer having a specified pattern on the gate dielectric layer;

forming sidewall insulation layers on side walls of the first conductive layer;

forming a source region and a drain region in the semiconductor layer;

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removing a part of the first conductive layer in a manner so that the gate dielectric layer is not exposed, to thereby form a recessed section on the first conductive layer between the sidewall insulation layers, wherein the removing a part of the first conductive layer is carried out after formation of the source region and the drain region;

forming a second conductive layer in a portion of the recessed section; and

forming an insulation layer in the recessed section on the second conductive layer.

10. (amended) A method for manufacturing a semiconductor device according to claim 9, further comprising, after forming the source region and the drain region and before removing a part of the first conductive layer:

forming a first insulating layer that covers the first conductive layer, the sidewall insulation layers, and the semiconductor layer; and

planarizing the first insulation layer so that the first conductive layer is exposed.

11. (amended) A method for manufacturing a semiconductor device according to claim 10, further comprising, after forming the insulation layer in the recessed section above the second conductive layer:

etching the first insulation layer to form a first through hole that reaches the source region or the drain region; and

forming a first contact layer in the first through hole.

12. (amended) A method for manufacturing a semiconductor device according to claim 9, wherein the second conductive layer comprises a silicide.

13. (amended) A method for manufacturing a semiconductor device according to claim 9, wherein the removing a part of the first conductive layer further includes removing a greater depth of the first conductive layer from a center region than from end regions adjacent to the sidewall insulation layers.

Please add new claim 24 as follows:

--24. A method for manufacturing a semiconductor device according to claim 9, wherein the first insulation layer comprises silicon oxide, and the second insulation layer comprises silicon nitride.--